CLAIMS:

What is claimed is:

1. A process for removing photoresist from semiconductor wafers comprising:

   (a) mixing said ozone with deionized water via a sparger plate; and

   (b) exposing semiconductor wafers having at least one layer of photoresist to said mixture of ozone and deionized water.

2. The process according to claim 1 further comprising the step of placing the semiconductor wafers within a processing tank.

3. The process according to claim 1 further comprising the maintaining the temperature in the processing tank at ambient temperature.

4. The process according to claim 3 wherein the temperature is about 20-21 ° C.

5. The process according to claim 3 wherein the temperature is above 20-21 ° C.

6. The process according to claim 1 wherein the mixture of ozone and deionized water is recirculated and flows back into the processing tank.

7. The process according to claim 1 wherein the mixture of deionized water and ozone is recirculated and ozone added so as to keep the concentration of ozone in said mixture about constant.

8. The process according to claim 7 wherein said mixture of deionized water and ozone is agitated via the sparger plate.